NSN 5962-01-370-0382

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View Online at https://aerobasegroup.com/nsn/5962-01-370-0382

view Online at https://aerobasegroup.com/hsh/osoz-on-oro-osoz
Maximum Power Dissipation Rating:
1.0 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
An/fps-124
Features Provided:
Programmed
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Bipolar metal-oxide semiconductor
Case Outline Source And Designator:
D-9 mil-m-38510
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit, digital, schottky, bipolar 8, 192 bit (1k x 8) programmable read only memory (prom), monolithic silicon
Voltage Rating And Type Per Characteristic:
-0.5 volts total supply and 7.0 volts total supply and 4.5 volts positive power supply span and 5.5 volts positive power supply span
Time Rating Per Chacteristic:
45.00 nanoseconds access
Memory Device Type:
Prom
Hybrid Technology Type:
Monolithic
Test Data Document:
81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-88
standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
24 printed circuit
Specification Data:
56232-1219252 manufacturers specification control
Specification Or Standard:

Shelf Life:

202 number

Departure From Cited Document:

Altered by programming, marking & testing

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Demilitarization:

Yes - demil/mli

Fiig:

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